

*Supplementary information for*

**Non-volatile ferroelectric modulation of room temperature electronic  
transport in La:BaSnO<sub>3</sub>/SrTiO<sub>3</sub>/PMN-PT heterostructures**

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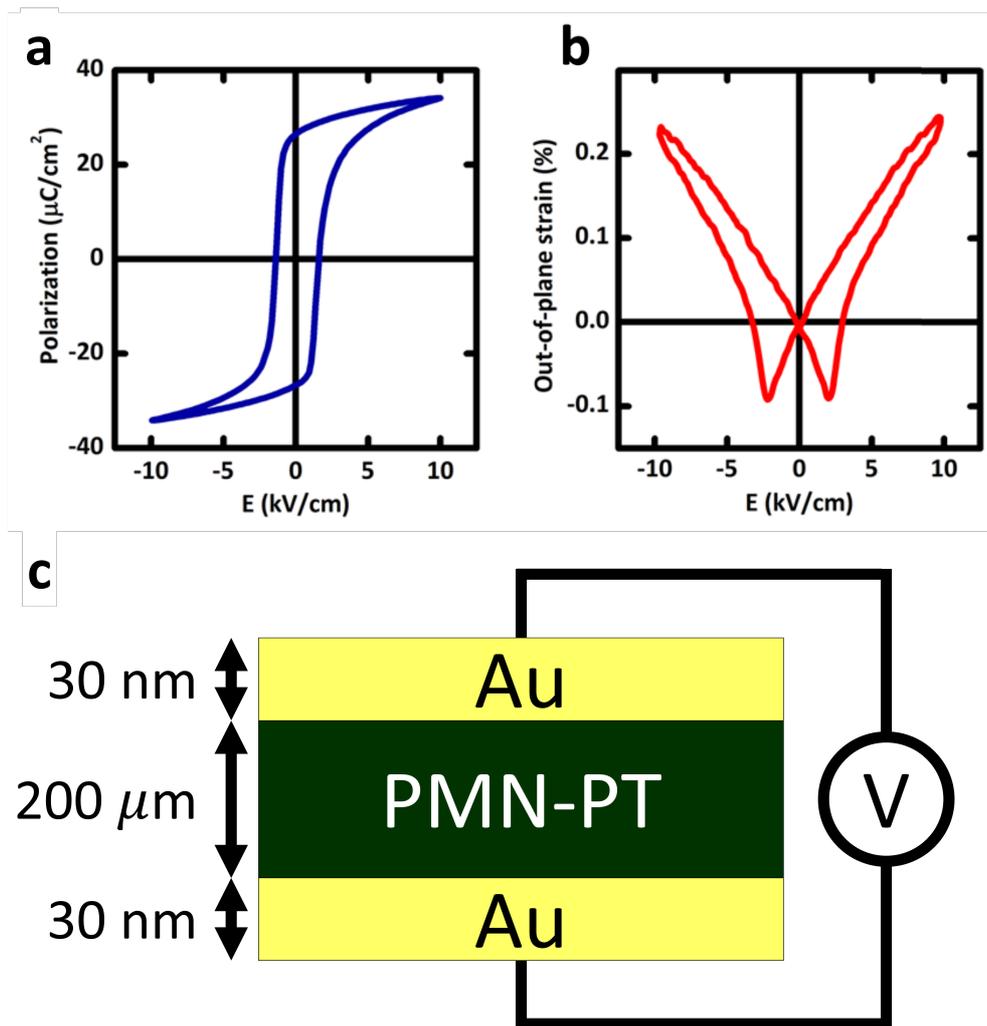
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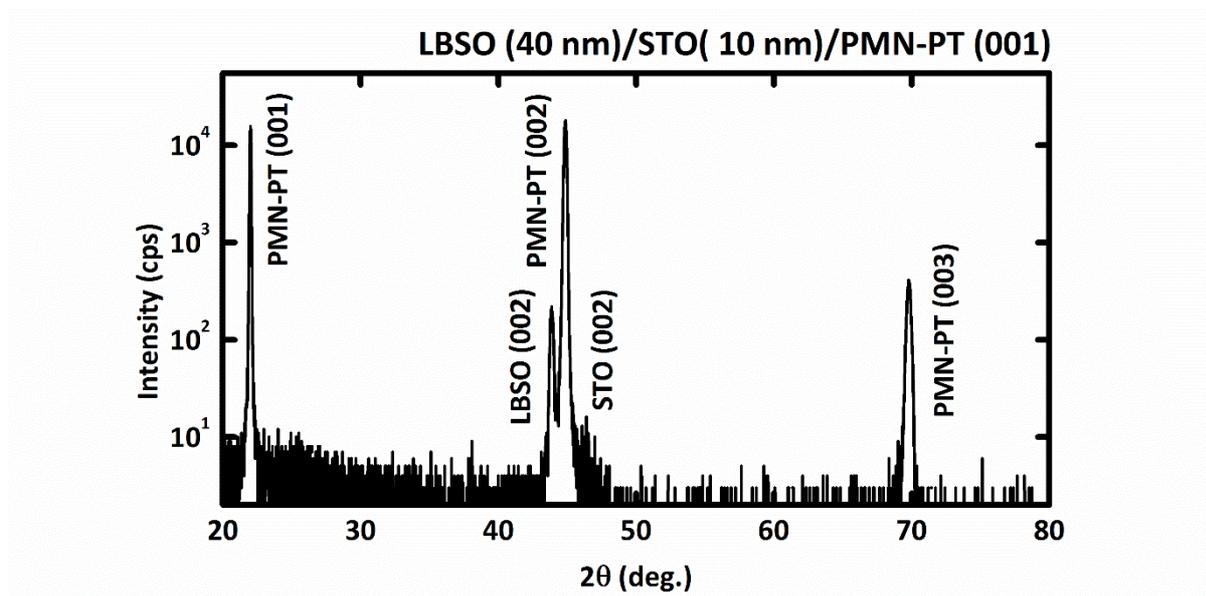
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	1% LBSO/PMN-PT ("w/o STO")	1% LBSO/STO/PMN-PT ("w/ STO")	1% LBSO on STO substrate
$\rho$ ( $\Omega\cdot\text{cm}$ )	1.58	$4.3 \times 10^{-2}$	$6.19 \times 10^{-3}$
$n$ ( $\text{cm}^{-3}$ )	$1.79 \times 10^{18}$	$1.57 \times 10^{19}$	$5.35 \times 10^{19}$
$\mu$ ( $\text{cm}^2 \text{V}^{-1} \text{s}^{-1}$ )	2.2	9.1	18.9

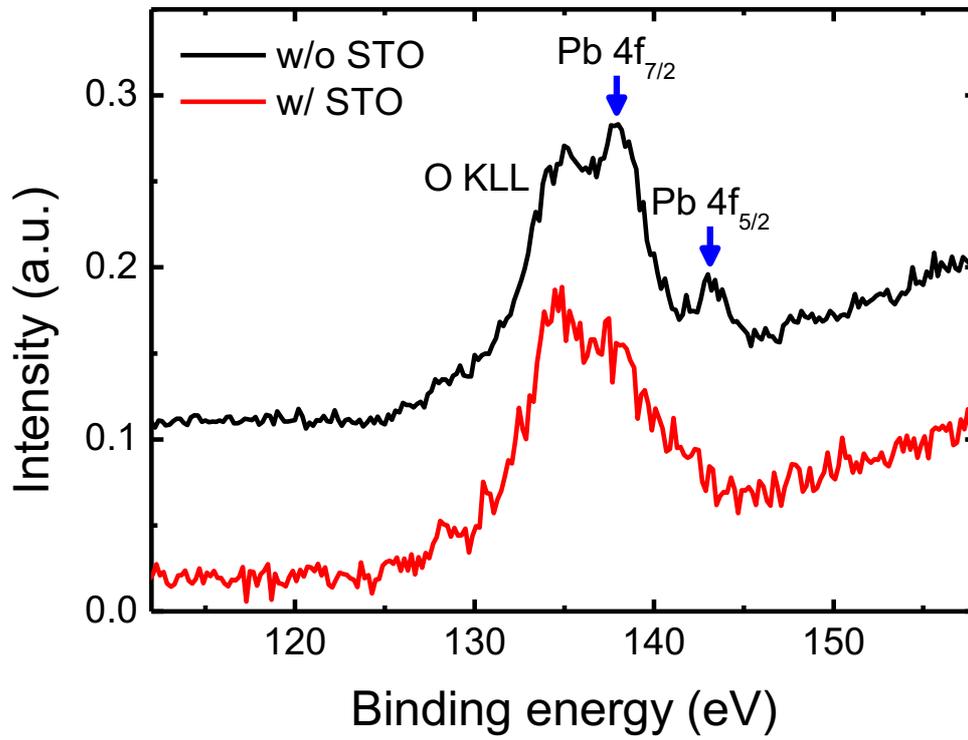
**Table S1 | Electrical resistivity, carrier concentration, and mobility of 1% La-doped BaSnO<sub>3</sub> thin films on PMN-PT (001) substrate with/without STO buffer layer and on STO (001) substrate.**



**Figure S1 | Ferroelectric and piezoelectric PMN-PT substrate.** (a) The P-E hysteresis loop for the PMN-PT substrate at 300 K. (b) Out-of-plane S-E curve for the PMN-PT substrate for the PMN-PT substrate at 300 K. (c) Illustration of the measurement. The converse piezoelectric behavior (S-E hysteresis) and the P-E hysteresis curves of PMN-PT single crystal substrate were measured at 300 K. (30 nm gold metal are used as top and bottom electrode). Laser Displacement Sensor (LK-G10, Keyence Co. Tokyo, Japan, 10 nm resolution with a spot size of  $20\ \mu\text{m}$ ) are used for S-E curve and a ferroelectric test system (P-LC100-K, Radiant Technologies, Albuquerque, NM) are used for P-E curve (10 Hz).



**Figure S2 | Wide angle XRD patterns of LBSO/STO/PMN-PT (001).** No impurity phases are observed within the detection level of XRD.



**Figure S3 | Synchrotron XPS of 10 nm-thick LBSO thin films with and without STO interlayer. Pb 4f peak appears at the samples without STO interlayer.**